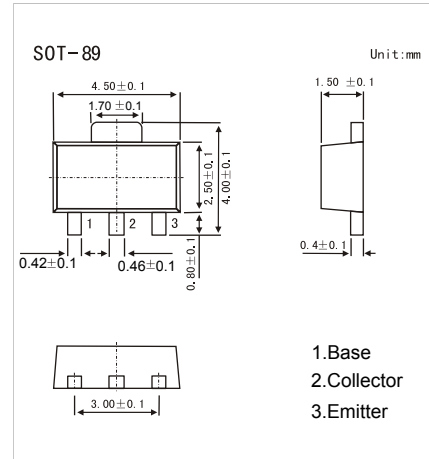


PNP Transistors

2SA1575

■ Features

- High fr.
- High breakdown voltage.
- Small reverse transfer capacitance and excellent high-frequency characteristic.
- Complementary to 2SC4080



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V <sub>CB0</sub>	-200	V
Collector - Emitter Voltage	V <sub>CE0</sub>	-200	
Emitter - Base Voltage	V <sub>EB0</sub>	-4	
Collector Current - Continuous	I <sub>c</sub>	-100	mA
Collector Current - Pulse	I <sub>CP</sub>	-200	
Collector Power Dissipation	P <sub>c</sub>	500	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature range	T <sub>stg</sub>	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V <sub>CB0</sub>	I <sub>c</sub> = -100 μA, I <sub>E</sub> =0	-200			V
Collector- emitter breakdown voltage	V <sub>CE0</sub>	I <sub>c</sub> = -1 mA, R <sub>BE</sub> = ∞	-200			
Emitter - base breakdown voltage	V <sub>EB0</sub>	I <sub>E</sub> = -100 μA, I <sub>c</sub> =0	-4			
Collector-base cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = -150 V, I <sub>E</sub> =0			-0.1	μA
Emitter cut-off current	I <sub>EB0</sub>	V <sub>EB</sub> = -3V, I <sub>c</sub> =0			-0.1	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> =-20 mA, I <sub>B</sub> =-2 mA			-1	V
Base - emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>c</sub> =-20 mA, I <sub>B</sub> =-2 mA			-1	
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = -10V, I <sub>c</sub> = -10mA	40		320	
		V <sub>CE</sub> = -10V, I <sub>c</sub> = -60mA	20			
Reverse Transfer Capacitance	C <sub>re</sub>	V <sub>CB</sub> = -30V, f=1MHz		1.7		pF
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -30V, f=1MHz		2.3		
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -30V, I <sub>c</sub> = -30mA		400		MHz

■ Classification of h<sub>FE</sub>

Type	2SA1575-C	2SA1575-D	2SA1575-E	2SA1575-F
Range	40-80	60-120	100-200	160-320
Marking	AFC	AFD	AFE	AFF